

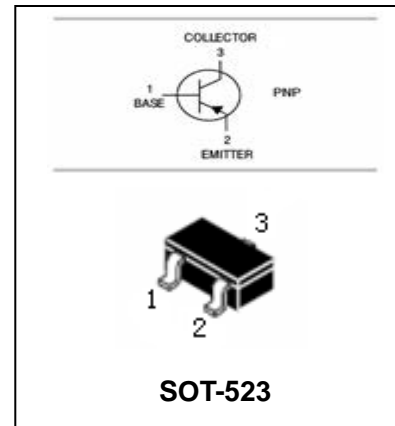
LOW FREQUENCY TRANSISTOR

2SA2018

FEATURES

- A collector current is large
- Collector saturation voltage is low
 $V_{CE(sat)} \leq 250\text{mV} @ I_C = -200\text{mA} / I_B = -10\text{mA}$

HF



APPLICATIONS

- For switching, for muting

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA2018	BW	SOT-523

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Limits	Unit
V_{CBO}	Collector-base Voltage	-15	V
V_{CEO}	Collector-emitter Voltage	-12	V
V_{EBO}	Emitter-base Voltage	-6	V
I_C	Collector Current	-500	mA
P_d	Collector Power Dissipation	150	mW
T_{STG}	Storage Temperature Range	-55 to +150	°C
T_J	Junction Temperature	150	°C

LOW FREQUENCY TRANSISTOR

2SA2018

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	Typ.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakown voltage	$I_C=-10\mu A, I_E=0$	-15			
$V_{(BR)CEO}$	Collector- emitter breakown voltage	$I_C=-1mA, I_B=0$	-12			
$V_{(BR)BEO}$	Emitter-base breakown voltage	$I_E=-10\mu A, I_C=0$	-6			
I_{CBO}	Collector cut-off current	$I_E=0, V_{CB}=-15V$			-100	nA
I_{EBO}	Emitter cut-off current	$I_C=0, V_{EB}=-6V$			-100	nA
h_{FE}	DC current gain	$V_{CE}=-2V, I_C=-10mA$	270		680	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C=-50mA, I_B=-5mA$		-100	-250	mV
C_{obo}	Output capacitance	$I_E=0, V_{CB}=-10V, f=1MHz$		6.5		pF
f_T	transition frequency	$I_E=10A, V_{CE}=-2V,$ $f=100MHz$		260		MHz

LOW FREQUENCY TRANSISTOR

2SA2018

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

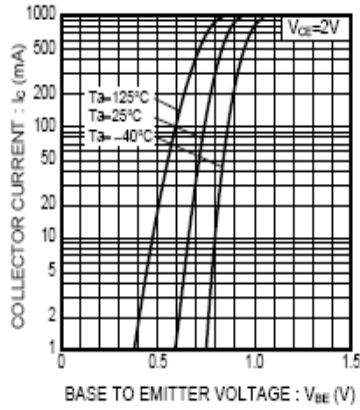


Fig.1 Grounded Emitter Propagation Characteristics

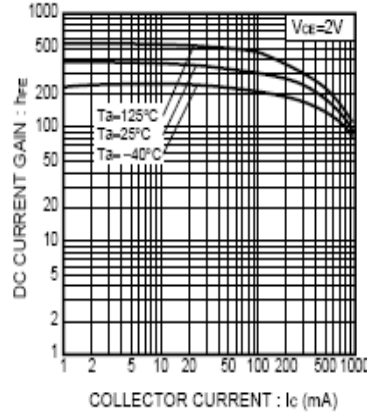


Fig.2 DC Current Gain vs. Collector Current

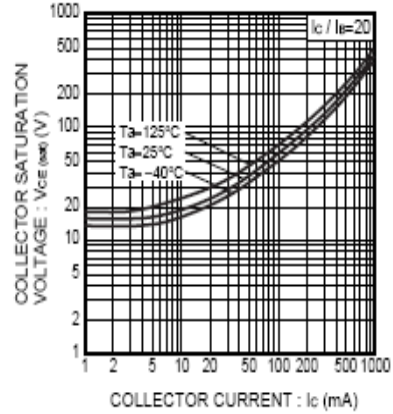


Fig.3 Collector-Emitter Saturation Voltage vs. Collector Current (I)

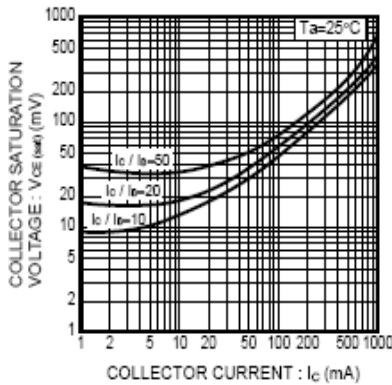


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (II)

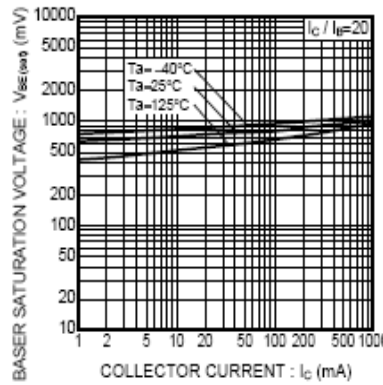


Fig.5 Base-Emitter Saturation Voltage vs. Collector Current

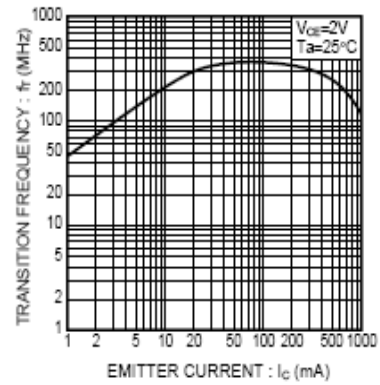


Fig.6 Gain Bandwidth Product vs. Emitter Current

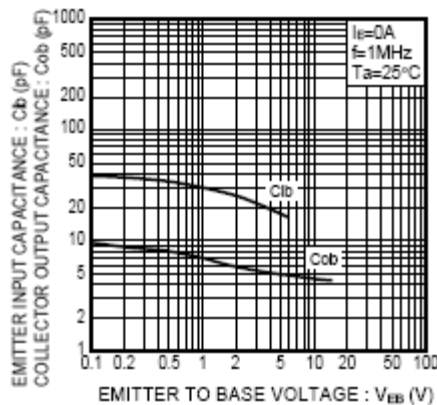


Fig.7 Collector Output Capacitance vs. Collector-Base Voltage
Emitter Input Capacitance vs. Emitter-Base Voltage

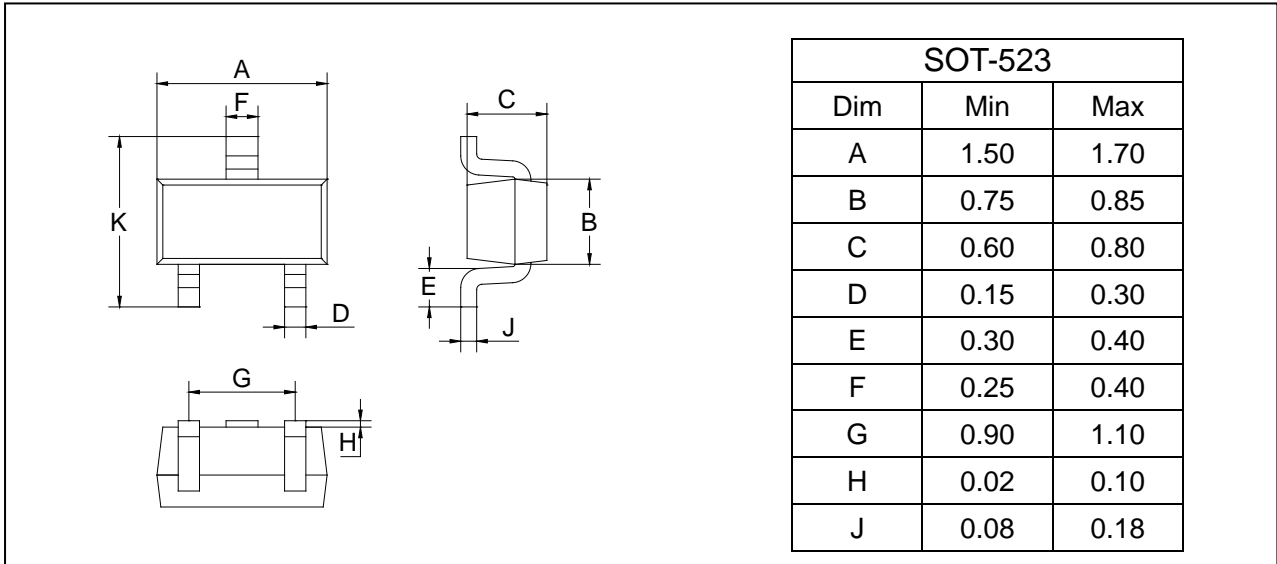
LOW FREQUENCY TRANSISTOR

2SA2018

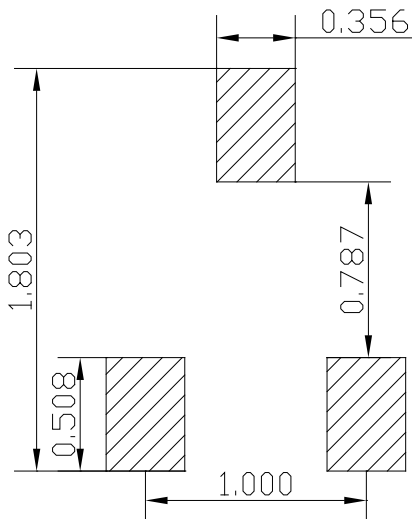
PACKAGE OUTLINE

Plastic surface mounted package

SOT-523



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SA2018	SOT-523	3000pcs / Tape & Reel